

#### 25V NPN LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

## **Description**

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

### **Features**

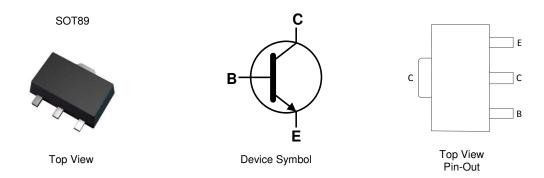
- BV<sub>CEO</sub> > 25V
- I<sub>C</sub> = 5.5A High Continuous Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Very Low Saturation Voltages
- Extremely Low Equivalent On-Resistance;  $R_{CE(SAT)} = 25m\Omega$  at 6.5A
- Excellent h<sub>FE</sub> Characteristics up to 20A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208<sup>3</sup>
- Weight: 0.05 grams (Approximate)

## **Applications**

- Emergency Lighting Circuits
- Motor Driving (Including DC Fans)
- · Solenoid, Relay and Actuator Drivers
- DC DC Modules
- Backlight Inverters



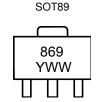
## Ordering Information (Note 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTN2005ZQTA	869	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

### **Marking Information**



869 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 8 = 2018) WW = Week Code (01 to 53)



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	5.5	Α
Peak Pulse Current	I <sub>CM</sub>	20	Α

# Thermal Characteristics (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)		1.5 12	W mW/°C	
Linear Derating Factor	(Note 7)	- P <sub>D</sub>	2.1 16.8		
Thermal Desistance, Junetian to Ambient Air	(Note 6)	D	83	°C/W	
Thermal Resistance, Junction to Ambient Air	(Note 7)	R <sub>0JA</sub>	60		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

#### Notes:

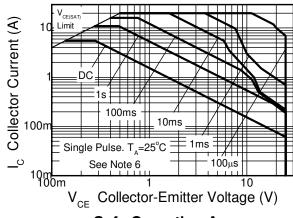
<sup>6.</sup> For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>7.</sup> Same as note (6), except the device is mounted on 50mm x 50mm 1oz copper.

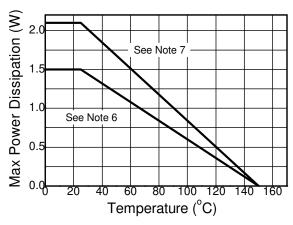
<sup>8.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



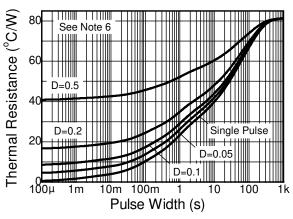
## **Thermal Characteristics and Derating Information**



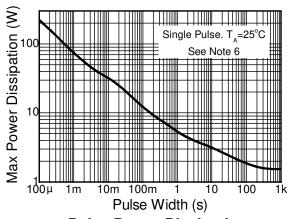
**Safe Operating Area** 



**Derating Curve** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



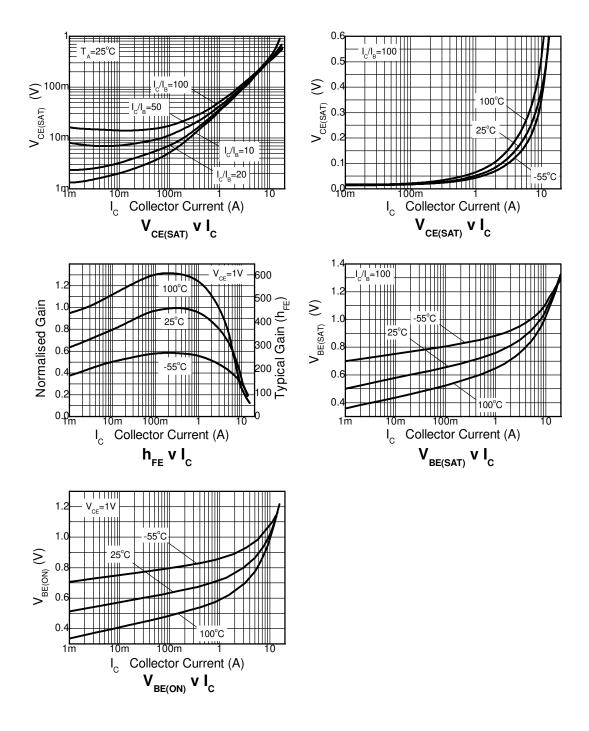
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	120	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	60	120	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	25	35	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	_	V	$I_E = 100\mu A$
Collector Cutoff Current	I <sub>CBO</sub>	_	_	20 0.5	nA μA	V <sub>CB</sub> = 50V V <sub>CB</sub> = 50V, T <sub>A</sub> = +100°C
Collector Cutoff Current	I <sub>CER</sub> R ≤ 1kΩ	_	_	20 0.5	nA μA	V <sub>CB</sub> = 50V V <sub>CB</sub> = 50V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	10	nA	V <sub>EB</sub> = 5.6V
DC Current Transfer Static Ratio (Note 9)	h <sub>FE</sub>	300 300 200 40	400 450 275 55	_	_	$I_{C} = 10 \text{mA}, V_{CE} = 1 \text{V}$ $I_{C} = 1 \text{A}, V_{CE} = 1 \text{V}$ $I_{C} = 7 \text{A}, V_{CE} = 1 \text{V}$ $I_{C} = 20 \text{A}, V_{CE} = 1 \text{V}$
Collector-Emitter Saturation Voltage (Note 9)	Vce(sat)	_	25 30 45 105 160	35 45 70 130 200	mV	$\begin{split} I_C &= 500\text{mA}, \ I_B = 10\text{mA} \\ I_C &= 1\text{A}, \ I_B = 100\text{mA} \\ I_C &= 1\text{A}, \ I_B = 10\text{mA} \\ I_C &= 2\text{A}, \ I_B = 10\text{mA} \\ I_C &= 6.5\text{A}, \ I_B = 150\text{mA} \end{split}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(SAT)}$	_	950	1050	mV	$I_C = 6.5A$ , $I_B = 150mA$
Base-Emitter Turn-on Voltage (Note 9)	$V_{BE(ON)}$	_	860	960	mV	$I_C = 6.5A, V_{CE} = 1V$
Transitional Frequency	f <sub>T</sub>	_	150	_	MHz	$I_C = 100$ mA, $V_{CE} = 10$ V, $f = 50$ MHz
Output Capacitance	C <sub>OBO</sub>	_	48	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Time	t <sub>ON</sub>		33		ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A,
Switching fille	t <sub>OFF</sub>		464		115	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note 9: Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ .



## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

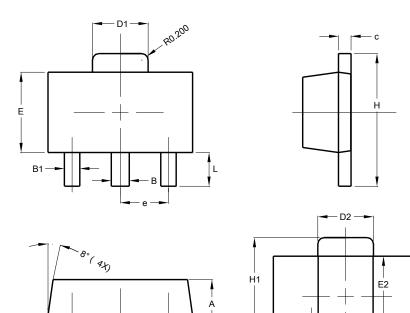




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT89

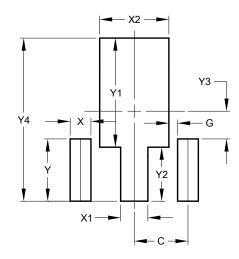


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT89



Dimensions	Value		
Dilliciisions	(in mm)		
С	1.500		
G	0.244		
X	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		

May 2018



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